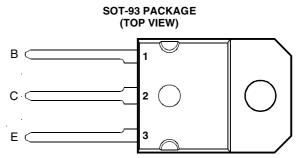


- Designed for Complementary Use with BDV65, BDV65A, BDV65B and BDV65C
- 125 W at 25°C Case Temperature
- 12 A Continuous Collector Current
- Minimum h_{FE} of 1000 at 4 V, 5 A



Pin 2 is in electrical contact with the mounting base.

MDTRAA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT	
	BDV64		-60		
Collector-base voltage (I _E = 0)	BDV64A		-80	V	
	BDV64B	V _{СВО}	-100		
	BDV64C		-120		
	BDV64		-60	V	
Collector-emitter voltage (I _B = 0)	BDV64A	.,	-80		
	BDV64B	V _{CEO}	-100		
	BDV64C		-120		
Emitter-base voltage		V _{EBO}	-5	V	
Continuous collector current	I _C	-12	Α		
Peak collector current (see Note 1)			-15	Α	
Continuous base current			-0.5	Α	
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)		P_{tot}	125	W	
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)			3.5	W	
Operating junction temperature range	P _{tot} T _j	-65 to +150	°C		
Storage temperature range	T _{stg}	-65 to +150	°C		
Lead temperature 3.2 mm from case for 10 seconds		T _L	260	°C	

NOTES: 1. This value applies for $t_p \le 0.1$ ms, duty cycle $\le 10\%$

- 2. Derate linearly to 150°C case temperature at the rate of 0.56 W/°C.
- 3. Derate linearly to 150°C free air temperature at the rate of 28 mW/°C.



electrical characteristics at 25°C case temperature (unless otherwise noted)

	PARAMETER		TEST	CONDITIONS		MIN	TYP	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C = -30 mA	I _B = 0	(see Note 4)	BDV64 BDV64A BDV64B BDV64C	-60 -80 -100 -120			٧
I _{CEO}	Collector-emitter cut-off current	$V_{CB} = -30 \text{ V}$ $V_{CB} = -40 \text{ V}$ $V_{CB} = -50 \text{ V}$ $V_{CB} = -60 \text{ V}$	$I_{B} = 0$ $I_{B} = 0$ $I_{B} = 0$ $I_{B} = 0$		BDV64 BDV64A BDV64B BDV64C			-2 -2 -2 -2	mA
Ісво	Collector cut-off current	V _{CB} = -120 V	I _E = 0	$T_{C} = 150^{\circ}C$ $T_{C} = 150^{\circ}C$ $T_{C} = 150^{\circ}C$ $T_{C} = 150^{\circ}C$	BDV64 BDV64A BDV64B BDV64C BDV64 BDV64A BDV64B BDV64C			-0.4 -0.4 -0.4 -0.4 -2 -2 -2	mA
I _{EBO}	Emitter cut-off current	V _{EB} = -5 V	I _C = 0					-5	mA
h _{FE}	Forward current transfer ratio	V _{CE} = -4 V	I _C = -5 A	(see Notes 4 and	1.5)	1000			
V _{CE(sat)}	Collector-emitter saturation voltage	I _B = -20 mA	I _C = -5 A	(see Notes 4 and	5)			-2	V
V _{BE}	Base-emitter voltage	V _{CE} = -4 V	I _C = -5 A	(see Notes 4 and	(5)			-2.5	V
V _{EC}	Parallel diode forward voltage	I _E = -10 A	$I_B = 0$	(see Notes 4 and	15)			-3.5	V

thermal characteristics

	PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to case thermal resistance			1	°C/W
$R_{\theta JA}$	Junction to free air thermal resistance			35.7	°C/W

NOTES: 4. These parameters must be measured using pulse techniques, t_p = 300 μs, duty cycle ≤ 2%.
 5. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

COLLECTOR-EMITTER SATURATION VOLTAGE

vs

TYPICAL CHARACTERISTICS

TYPICAL DC CURRENT GAIN vs **COLLECTOR CURRENT** TCS145AD 10000 -40°C 25°C = 100°C h_{FE} - Typical DC Current Gain 1000 $V_{CE} =$ -4 V = 300 μ s, duty cycle < 2% 100 -0.5 -1.0 -10 -20 I_c - Collector Current - A

Figure 1.

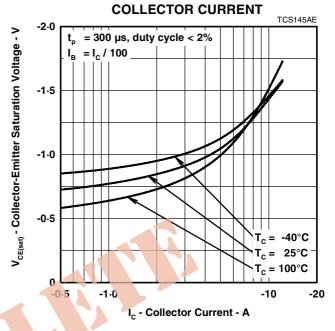


Figure 2.

BASE-EMITTER SATURATION VOLTAGE

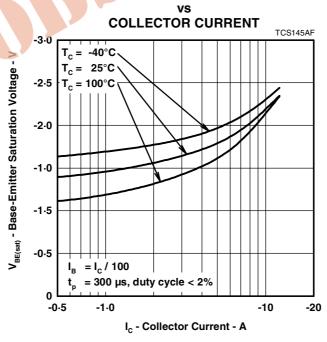


Figure 3.

THERMAL INFORMATION

MAXIMUM POWER DISSIPATION

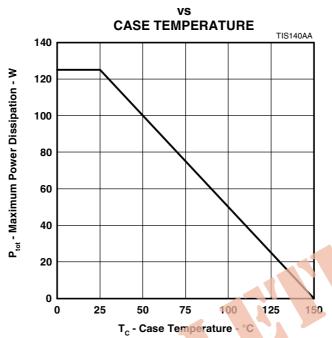


Figure 4.